

High purity silicon carbide powders for semiconductor and electronic applications.

High purity silicon carbide produced by the Acheson process for semiconductor and electronic applications. Particularly suitable for PVT crystal growth for SiC wafer manufacturing.

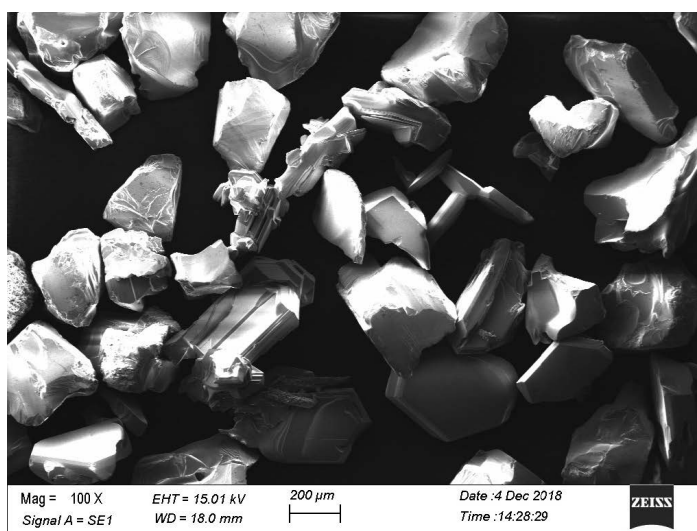
Typical chemistry

Element	Concentration [ppm wt]	Element	Concentration [ppm wt]
Al	5.9	Na	0.62
B	0.23	Ni	0.33
Ba	0.05	P	0.13
C	Matrix	Si	Matrix
Ca	0.67	S	1.6
Cl	1.5	Ti	2.8
Cr	0.41	V	0.19
Cu	0.18	Zn	0.45
F	< 0.1	Zr	0.22

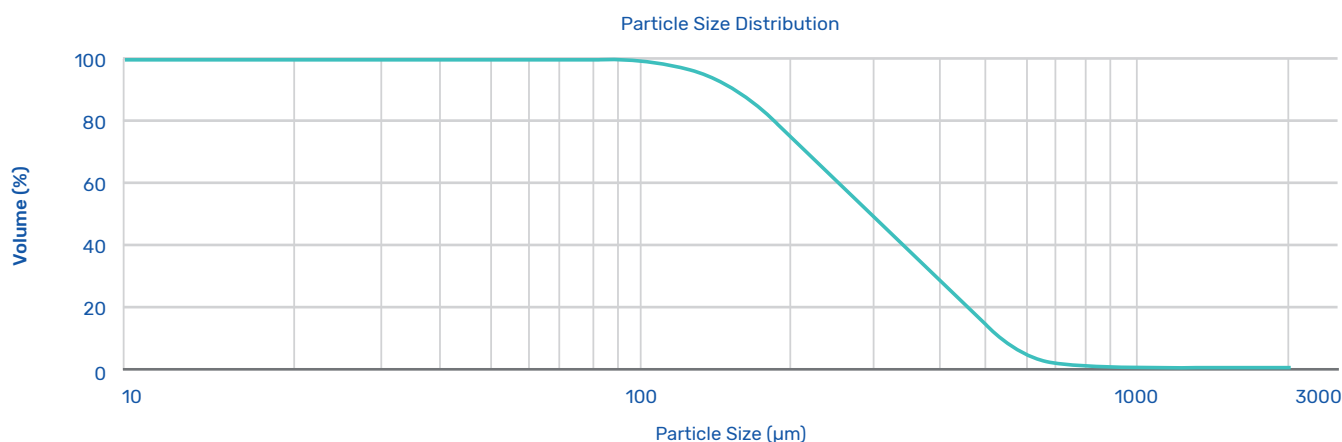
In Binder

Analysis by GDMS

Element	Measurement	Unit	Instrument
Free C	0.01	% wt	Carbolite
Total oxygen	0.02	% wt	LECO



Typical size distribution curve (Malvern Mastersizer)



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